

AMENDMENTS TO THE SPECIFICATION

Please replace paragraph [0029] with the following amended paragraph:

[0029] In the liquid crystal display described with respect to FIG. 4, an active layer of, e.g., amorphous silicon $[(a\text{-Sh:H})]$ (a-Si:H) material, on a lower layer of pixels controlled by the number one scanning line or gate line (G1) (see FIG. 2) serves to restrict a transmission of light to pixel electrodes and to restrict the line light phenomenon. Accordingly, this active layer may also be referred to as a light transmission restricting layer.

Please replace paragraph [0037] with the following amended paragraph:

[0037] As shown in FIG. 5b, the light transmission restricting layer 53 of the amorphous silicon $[(a\text{-Sh:H})]$ (a-Si:H) material is evaporated on the gate insulating film 52 using the PECVD method, and then patterned through a photolithography process, an etching process and a strip process. Beneficially, the light transmission restricting layer 53 is the same as the amorphous silicon layer, which is a channel layer of the TFT, and thereby the active layer is formed when the channel layer of the TFT is formed, without any additional process.

Please replace paragraph [0043] with the following amended paragraph:

[0043] Furthermore, when the channel layer of the TFT is formed, the ~~active~~ light transmission restricting layer is formed without requiring additional process, thereby changing the thickness and the area of the active layer through the existing process.